

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IFW

In re Applicant:

Yair EIN-ELI et al

Serial No.: 10/750,969

Filed: January 5, 2004

For: Texturing A Semiconductor Material ...

Group Art Unit: 1742

Attorney
Docket: 27054

Commissioner for Patents
PO Box 1450
Alexandria, VA 22313-1450

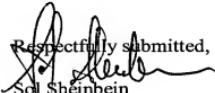


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Sir:

Enclosed is a PTO Form 1449 which lists citations which may be material to the patentability and examination of the above identified application. Also enclosed are copies of the references cited. These are submitted in compliance with the duty of disclosure defined in 37 CFR 1.56. The Examiner is requested to make these citations of official record in this application.

This Information Disclosure Statement under 37 CFR 1.56 is not to be construed as a representation that a search has been made, that additional matter which is material to the examination of this application does not exist, or that any or more of these citations constitutes prior art.

Respectfully submitted,

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Sheet 1 Of 2 Attorney Docket Number 27054

U.S. PATENT DOCUMENTS

Examiners Initials	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, columns, lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
		6,340,640		Nishimoto et al	01-22-2002	
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Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			T ²
		Ein-Eli et al., "Silicon Texturing Under Negative Potential Dissolution (NPD)", <i>Int. Soc. Electrochemistry, Ann. Mtg.</i> , Thessaloniki, 19-24-Sept., 2004			
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